

Description

The SI2319 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

 $V_{DS} = -40V, I_{D} = -5A$

 $R_{DS(ON)}$ <85m Ω @ V_{GS} =-10V

 $R_{DS(ON)}$ <120m Ω @ V_{GS} =-4.5V

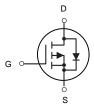


Application

Power switching application

Hard switched and high frequency circuits

DC-DC converter



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
SI2319	SOT-23	2319	3000

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	-40	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	-5	А
Drain Current-Continuous(T _C =100°C)	I _D (100°C)	-2.3	А
Pulsed Drain Current	I _{DM}	-18	Α
Maximum Power Dissipation	P _D	1.4	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}$
Thermal Resistance ,Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	89	°C/W



Electrical Characteristics (T_A=25 [°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	I _{GSS}	$V_{GS}=\pm20V, V_{DS}=0V$	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-1.0	-1.9	-3.0	V
Dunin Course On Chata Basistanas	Б	V _{GS} =-10V, I _D =-3A	-	73	85	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-2A	-	98	120	mΩ
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-3A	-	5	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	V _{DS} =-20V,V _{GS} =0V, F=1.0MHz	-	600	-	PF
Output Capacitance	Coss		-	90	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVID2	-	70	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	9	-	nS
Turn-on Rise Time	t _r	V_{DD} =-20 V , R_L =2 Ω	-	8	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10 V , R_{GEN} =3 Ω	-	28	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg	V 20VI 2A	-	14	-	nC
Gate-Source Charge	Q _{gs}	$V_{DS}=-20V, I_{D}=-3A,$	-	2.9	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =-10V	-	3.8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-3.3A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	-3.3	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

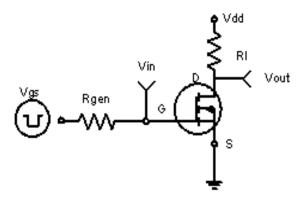


Figure 1:Switching Test Circuit

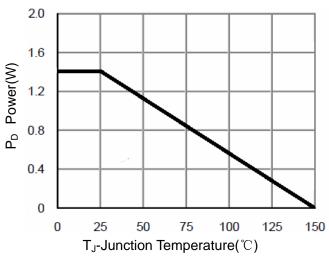


Figure 3 Power Dissipation

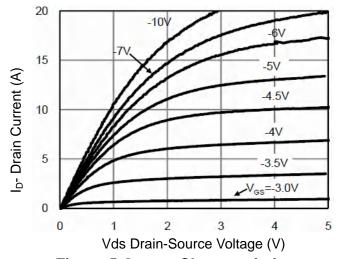


Figure 5 Output Characteristics

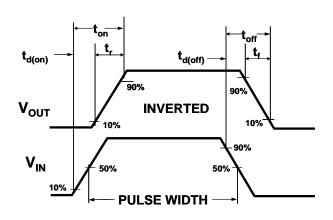


Figure 2:Switching Waveforms

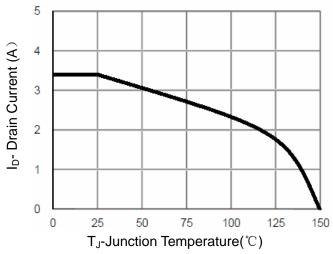


Figure 4 Drain Current

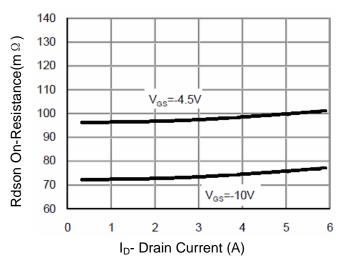


Figure 6 Drain-Source On-Resistance



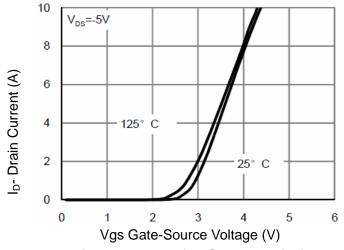


Figure 7 Transfer Characteristics

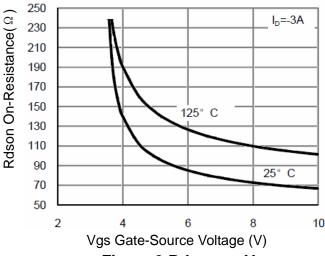
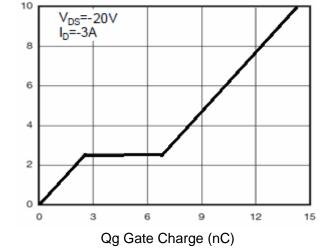


Figure 9 Rdson vs Vgs



Vgs Gate-Source Voltage (V)

Figure 11 Gate Charge

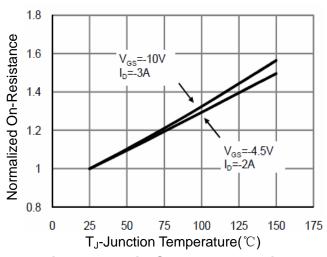


Figure 8 Drain-Source On-Resistance

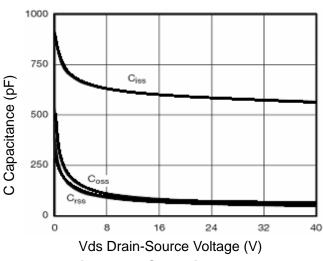


Figure 10 Capacitance vs Vds

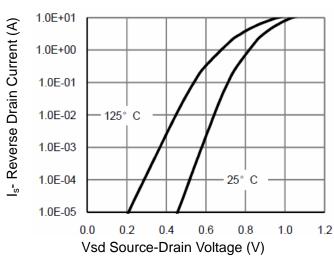


Figure 12 Source- Drain Diode Forward



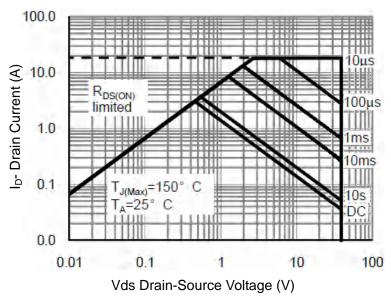


Figure 13 Safe Operation Area

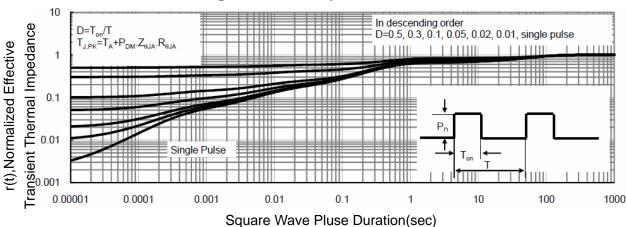
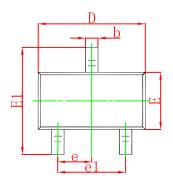
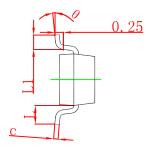


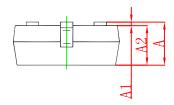
Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Outline Dimensions

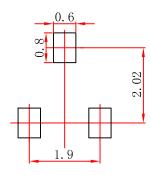






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



- Note: 1.Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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